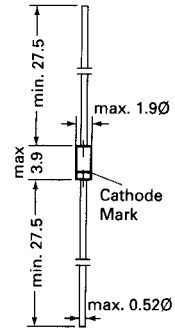
ST 60 P
SILICON SCHOTTKY BARRIER DIODE

Silicon Schottky Barrier Diode
Characteristics equivalent to or better than 1N60P ideal for used in detection or for switching on the radio, TV, etc..



Glass case JEDEC DO-35

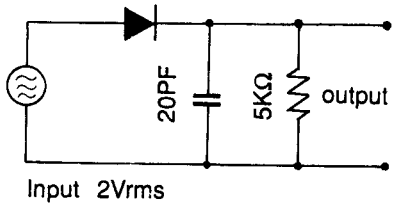
Dimensions in mm

Absolute Maximum Ratings (T_a= 25 °C)

	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	45	V
Reverse Voltage dc	V_R	20	V
Peak Forward Current	I_{FM}	150	mA
Average Rectified Output Current	I_O	50	mA
Surge Forward Current	I_{surge}	500	mA
Junction Temperature	T_j	75	°C
Storage Temperature Range	T_S	-55 to + 175	°C

Characteristics

	Symbol	Test condition (T_a 25 ± 2 °C)	Min.	Typ.	Max.	Units
Forward Current	I_F	V_F =1V	4	-	-	mA
Reverse Currents	I_R	V_R = 10V	-	-	50	µA
Junction Capacitance C	-	f = 1MHz,V = 1V	-	-	1	PF
Rectification efficiency	η	Vi = 2Vrms, =5KΩ C = 20PF, f = 40 MHz	55	-	-	%



Rectification Efficiency Measurement Circuit